Unit: mm

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

# 2SA1451A

#### High-Speed, High-Current Switching Applications

- · Low collector saturation voltage
  - $: V_{CE (sat)} = -0.4 \text{ V (max) (IC} = -6 \text{ A)}$
- High-speed switching:  $t_{stg} = 1.0 \mu s$  (typ.)
- Complementary to 2SC3709A

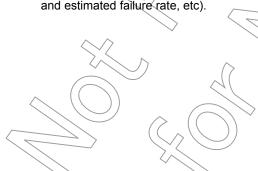
### Absolute Maximum Ratings (Tc = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	-60	$(\checkmark)$
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-6	V
Collector current	IC	-12	A
Base current	ΙΒ	-2	Α
Collector power dissipation	Pc 〈	90	VAT
(Tc = 25°C)	FC (	30	
Junction temperature	Tj	150	°C
Storage temperature range	T <sub>stg</sub>		°C

Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in

temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

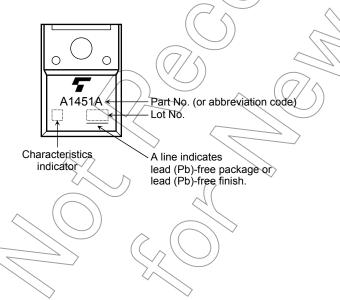


## **Electrical Characteristics (Tc = 25°C)**

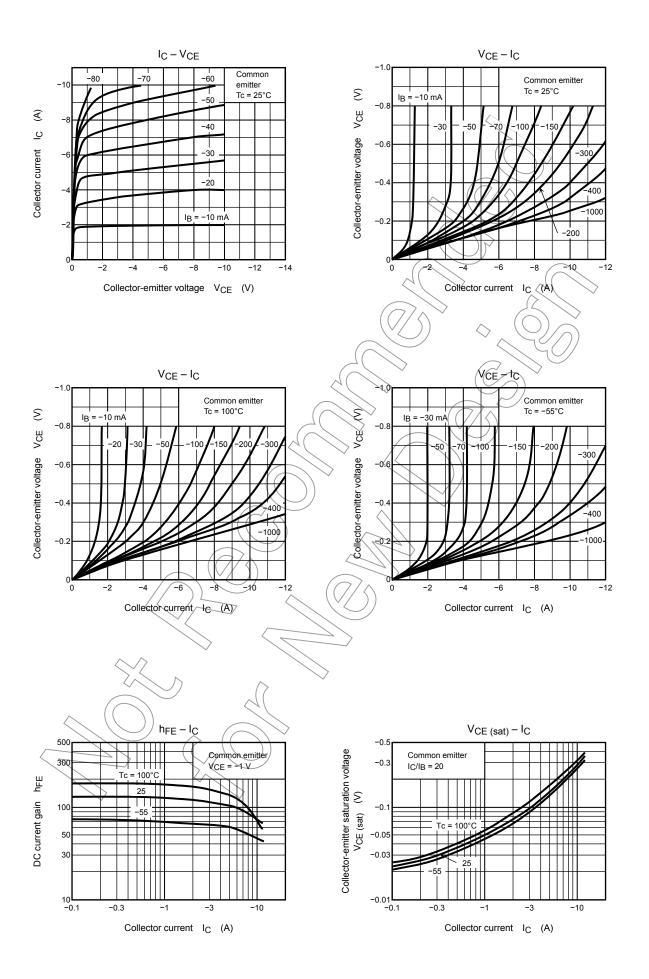
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off of	current	I <sub>CBO</sub>	$V_{CB} = -60 \text{ V}, I_E = 0$	_	_	-10	μΑ
Emitter cut-off cu	rrent	I <sub>EBO</sub>	V <sub>EB</sub> = -6 V, I <sub>C</sub> = 0	_	_	-10	μΑ
Collector-emitter	breakdown voltage	V (BR) CEO	$I_C = -50 \text{ mA}, I_B = 0$	-50	_	_	V
DC current gain		h <sub>FE (1)</sub> (Note)	V <sub>CE</sub> = -1 V, I <sub>C</sub> = -1 A	70	7	240	
		h <sub>FE (2)</sub>	V <sub>CE</sub> = -1 V, I <sub>C</sub> = -6 A	40	_	1	
Collector-emitter	saturation voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = -6 A, I <sub>B</sub> = -0.3 A	$\bigcirc )$	-0.15	-0.4	V
Base-emitter satu	uration voltage	V <sub>BE (sat)</sub>	I <sub>C</sub> = -6 A, I <sub>B</sub> = -0.3 A	_	-0.9	-1.2	V
Transition freque	ncy	f <sub>T</sub>	V <sub>CE</sub> = -5 V, I <sub>C</sub> = -1 A	_	70	_	MHz
Collector output of	capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz	_	320	/	pF
Switching time	Turn-on time	t <sub>on</sub>	20 μs Input 1B2 Output	_(	0.3	> -	μs
	Storage time	t <sub>stg</sub>	V <sub>CC</sub> ≈ -30 V		> 1.0	_	
	Fall time	t <sub>f</sub>	VCC ~ -30 V -I <sub>B1</sub> = I <sub>B2</sub> = 0.3 A, duty cycle ≤ 1%		0.2	_	

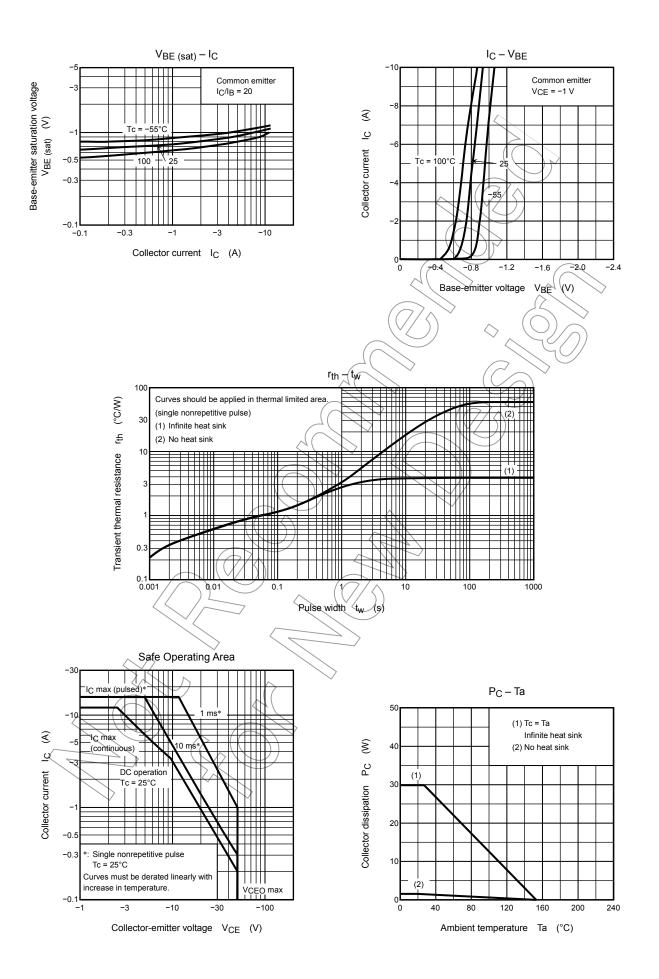
Note: h<sub>FE</sub> (1) classification O: 70 to 140, Y: 120 to 240

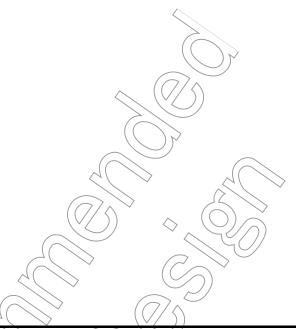




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